

**PowerMOS transistor
Logic level FET**

BUK583-60A

GENERAL DESCRIPTION

N-channel enhancement mode logic level field-effect power transistor in a plastic envelope suitable for surface mount applications.
The device is intended for use in automotive and general purpose switching applications.

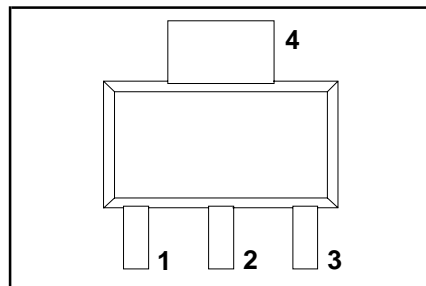
QUICK REFERENCE DATA

| SYMBOL | PARAMETER | MAX. | UNIT |
|--------------|---|------|------|
| V_{DS} | Drain-source voltage | 60 | V |
| I_D | Drain current (DC) | 3.2 | A |
| P_{tot} | Total power dissipation | 1.8 | W |
| T_j | Junction temperature | 150 | °C |
| $R_{DS(ON)}$ | Drain-source on-state resistance; $V_{GS} = 5\text{ V}$ | 0.10 | Ω |

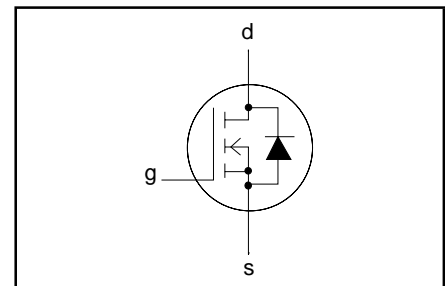
PINNING - SOT223

| PIN | DESCRIPTION |
|-----|-------------|
| 1 | gate |
| 2 | drain |
| 3 | source |
| 4 | drain (tab) |

PIN CONFIGURATION



SYMBOL



LIMITING VALUES

Limiting values in accordance with the Absolute Maximum System (IEC 134)

| SYMBOL | PARAMETER | CONDITIONS | MIN. | MAX. | UNIT |
|--------------|----------------------------------|---------------------------------------|------|------|------|
| V_{DS} | Drain-source voltage | - | - | 60 | V |
| V_{DGR} | Drain-gate voltage | $R_{GS} = 20\text{ k}\Omega$ | - | 60 | V |
| $\pm V_{GS}$ | Gate-source voltage | - | - | 15 | V |
| I_D | Drain current (DC) | $T_{amb} = 25\text{ }^\circ\text{C}$ | - | 3.2 | A |
| I_D | Drain current (DC) | $T_{amb} = 100\text{ }^\circ\text{C}$ | - | 2.0 | A |
| I_{DM} | Drain current (pulse peak value) | $T_{amb} = 25\text{ }^\circ\text{C}$ | - | 13 | A |
| P_{tot} | Total power dissipation | $T_{amb} = 25\text{ }^\circ\text{C}$ | - | 1.8 | W |
| T_{stg} | Storage temperature | - | - 55 | 150 | °C |
| T_j | Junction temperature | - | - | 150 | °C |

THERMAL RESISTANCES

| SYMBOL | PARAMETER | CONDITIONS | MIN. | TYP. | MAX. | UNIT |
|-----------------|--|--------------------------|------|------|------|------|
| $R_{th\ j-sp}$ | From junction to solder point ¹ | Mounted on any PCB | - | 12 | 15 | K/W |
| $R_{th\ j-amb}$ | From junction to ambient | Mounted on PCB of fig.18 | - | - | 70 | K/W |

¹ Temperature measured at solder joint on drain tab.

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STATIC CHARACTERISTICS

$T_j = 25\text{ °C}$ unless otherwise specified

| SYMBOL | PARAMETER | CONDITIONS | MIN. | TYP. | MAX. | UNIT |
|---------------|----------------------------------|--|------|------|------|---------------|
| $V_{(BR)DSS}$ | Drain-source breakdown voltage | $V_{GS} = 0\text{ V}; I_D = 0.25\text{ mA}$ | 60 | 70 | - | V |
| $V_{GS(TO)}$ | Gate threshold voltage | $V_{DS} = V_{GS}; I_D = 1\text{ mA}$ | 1.0 | 1.5 | 2.0 | V |
| I_{DSS} | Zero gate voltage drain current | $V_{DS} = 60\text{ V}; V_{GS} = 0\text{ V}; T_j = 125\text{ °C}$ | - | 1 | 10 | μA |
| I_{DSS} | Zero gate voltage drain current | $V_{DS} = 60\text{ V}; V_{GS} = 0\text{ V}; T_j = 125\text{ °C}$ | - | 0.1 | 1.0 | mA |
| I_{GSS} | Gate source leakage current | $V_{GS} = \pm 15\text{ V}; V_{DS} = 0\text{ V}$ | - | 10 | 100 | nA |
| $R_{DS(ON)}$ | Drain-source on-state resistance | $V_{GS} = 5\text{ V}; I_D = 3.2\text{ A}$ | - | 0.08 | 0.10 | Ω |

DYNAMIC CHARACTERISTICS

$T_j = 25\text{ °C}$ unless otherwise specified

| SYMBOL | PARAMETER | CONDITIONS | MIN. | TYP. | MAX. | UNIT |
|--------------|--------------------------|---|------|------|------|------|
| g_{fs} | Forward transconductance | $V_{DS} = 25\text{ V}; I_D = 3.2\text{ A}$ | - | 6.0 | - | S |
| C_{iss} | Input capacitance | $V_{GS} = 0\text{ V}; V_{DS} = 25\text{ V}; f = 1\text{ MHz}$ | - | 650 | 825 | pF |
| C_{oss} | Output capacitance | $V_{GS} = 0\text{ V}; V_{DS} = 25\text{ V}; f = 1\text{ MHz}$ | - | 240 | 350 | pF |
| C_{rss} | Feedback capacitance | $V_{GS} = 0\text{ V}; V_{DS} = 25\text{ V}; f = 1\text{ MHz}$ | - | 120 | 160 | pF |
| $t_{d\ on}$ | Turn-on delay time | $V_{DD} = 30\text{ V}; I_D = 3\text{ A}; V_{GS} = 5\text{ V}; R_{GS} = 50\text{ }\Omega;$ | - | 10 | 20 | ns |
| t_r | Turn-on rise time | $V_{GS} = 5\text{ V}; R_{GS} = 50\text{ }\Omega;$ | - | 35 | 55 | ns |
| $t_{d\ off}$ | Turn-off delay time | $R_{gen} = 50\text{ }\Omega$ | - | 60 | 90 | ns |
| t_f | Turn-off fall time | $R_{gen} = 50\text{ }\Omega$ | - | 55 | 80 | ns |

REVERSE DIODE LIMITING VALUES AND CHARACTERISTICS

$T_j = 25\text{ °C}$ unless otherwise specified

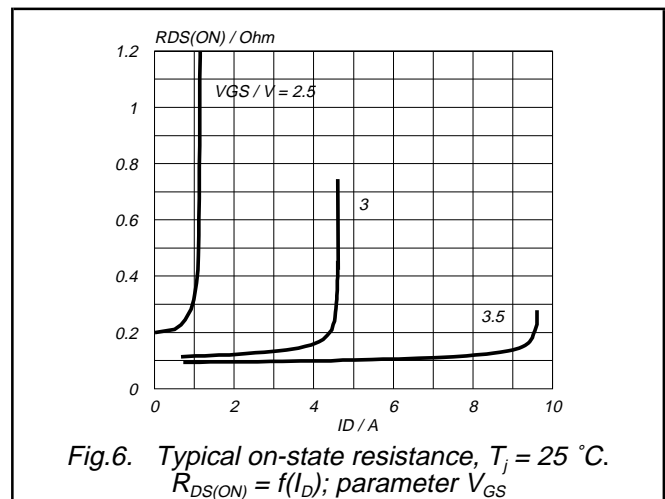
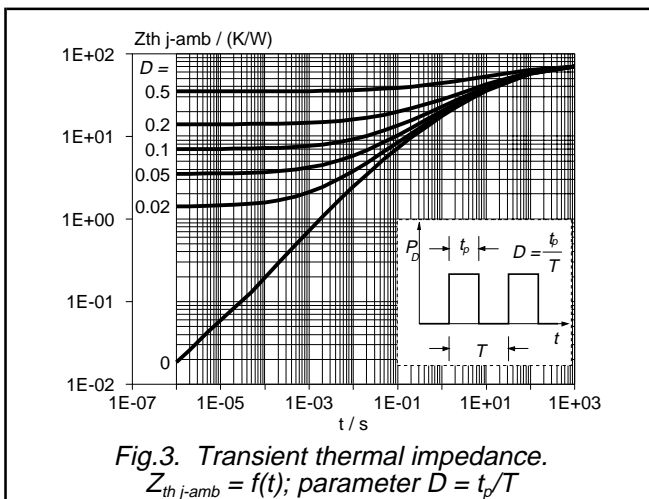
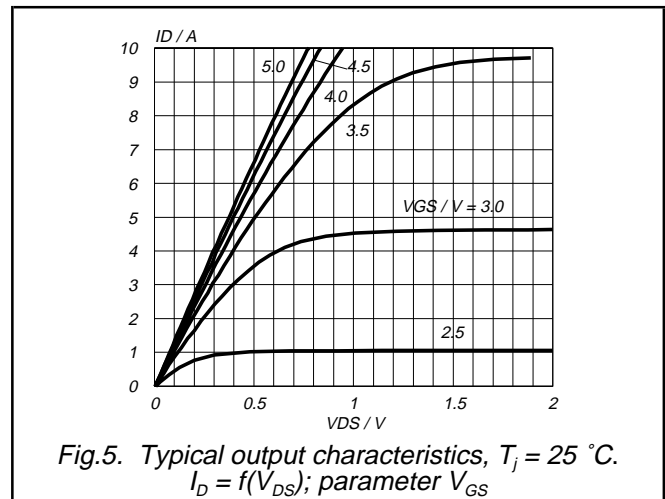
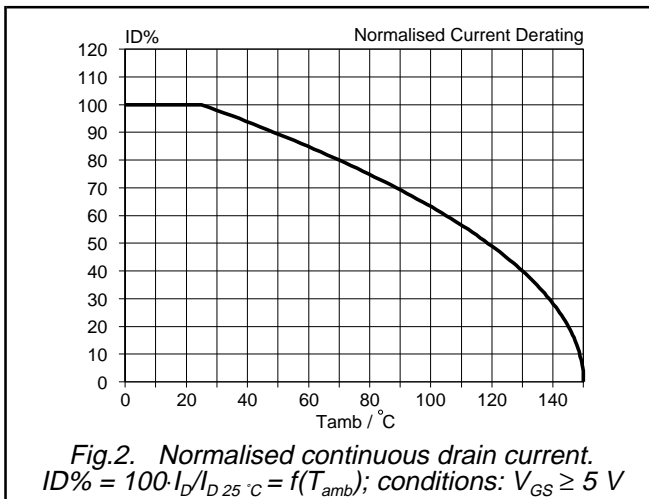
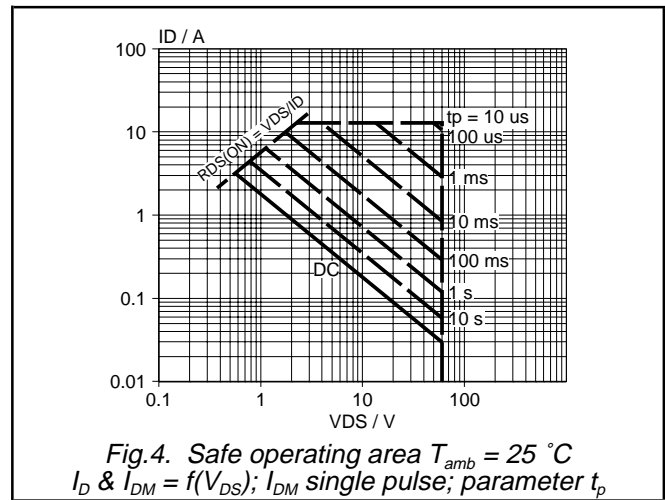
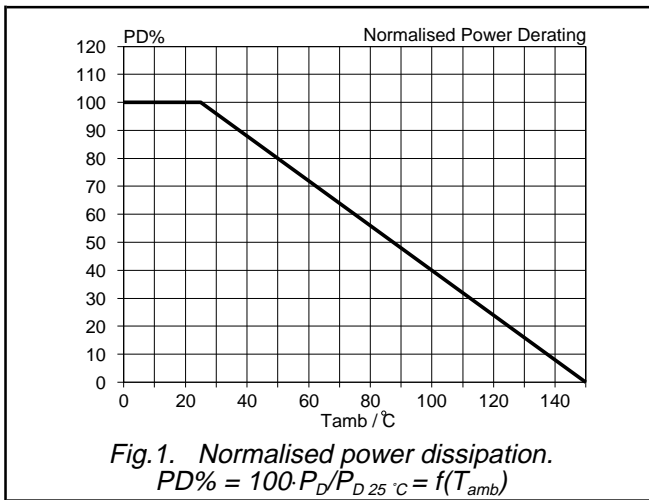
| SYMBOL | PARAMETER | CONDITIONS | MIN. | TYP. | MAX. | UNIT |
|-----------|----------------------------------|---|------|------|------|---------------|
| I_{DR} | Continuous reverse drain current | - | - | - | 3.2 | A |
| I_{DRM} | Pulsed reverse drain current | - | - | - | 13 | A |
| V_{SD} | Diode forward voltage | $I_F = 3.2\text{ A}; V_{GS} = 0\text{ V}$ | - | 0.85 | 1.1 | V |
| t_{rr} | Reverse recovery time | $I_F = 3.2\text{ A}; -di_F/dt = 100\text{ A}/\mu\text{s}; V_{GS} = -10\text{ V}; V_R = 30\text{ V}$ | - | 70 | - | ns |
| Q_{rr} | Reverse recovery charge | $I_F = 3.2\text{ A}; -di_F/dt = 100\text{ A}/\mu\text{s}; V_{GS} = -10\text{ V}; V_R = 30\text{ V}$ | - | 0.25 | - | μC |

AVALANCHE LIMITING VALUE

| SYMBOL | PARAMETER | CONDITIONS | MIN. | TYP. | MAX. | UNIT |
|-----------|---|---|------|------|------|------|
| W_{DSS} | Drain-source non-repetitive unclamped inductive turn-off energy | $I_D = 3.2\text{ A}; V_{DD} \leq 25\text{ V}; V_{GS} = 5\text{ V}; R_{GS} = 50\text{ }\Omega; T_{amb} = 25\text{ °C}$ | - | - | 45 | mJ |

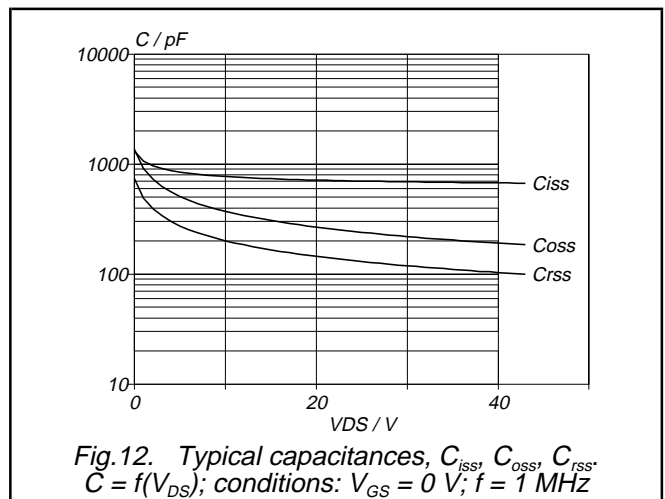
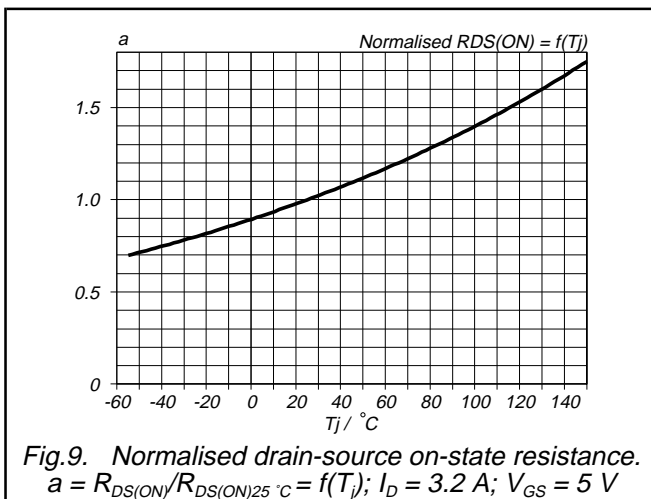
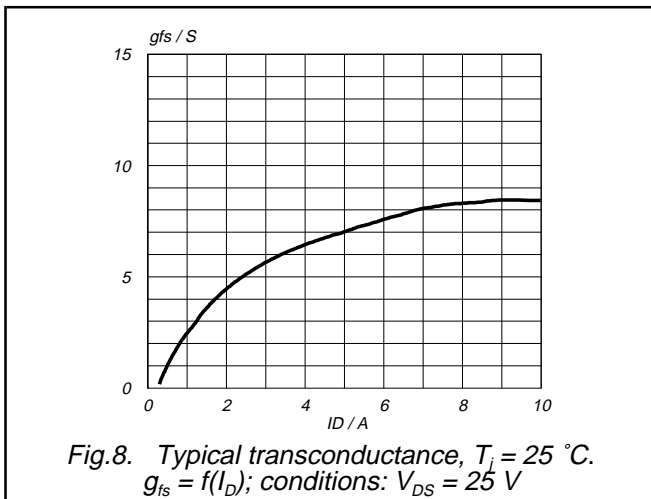
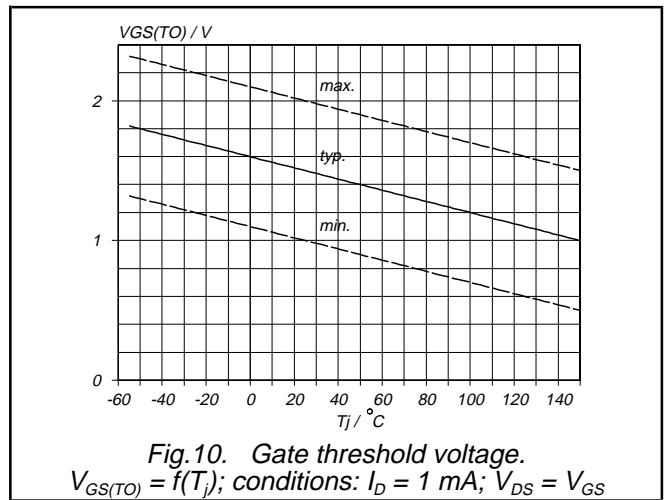
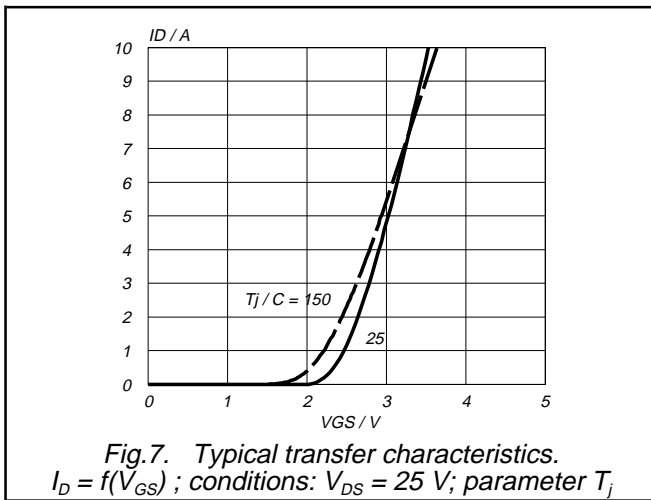
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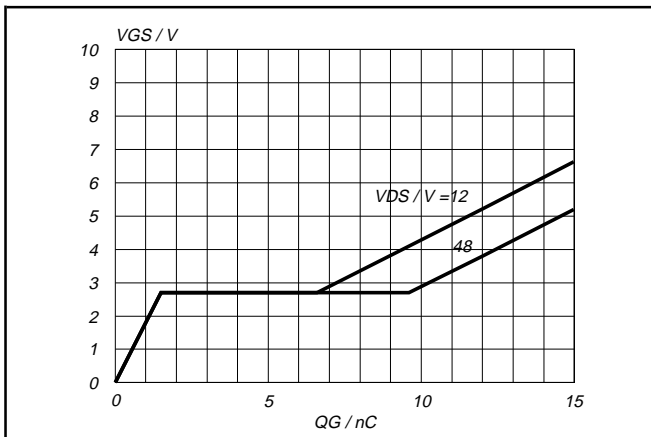


Fig. 13. Typical turn-on gate-charge characteristics.
 $V_{GS} = f(Q_G)$; conditions: $I_D = 3.2 \text{ A}$; parameter V_{DS}

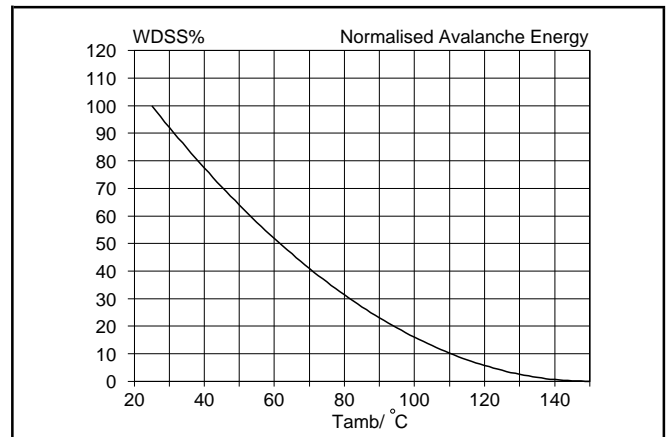


Fig. 15. Normalised avalanche energy rating.
 $W_{DSS}\% = f(T_{amb})$; conditions: $I_D = 3.2 \text{ A}$

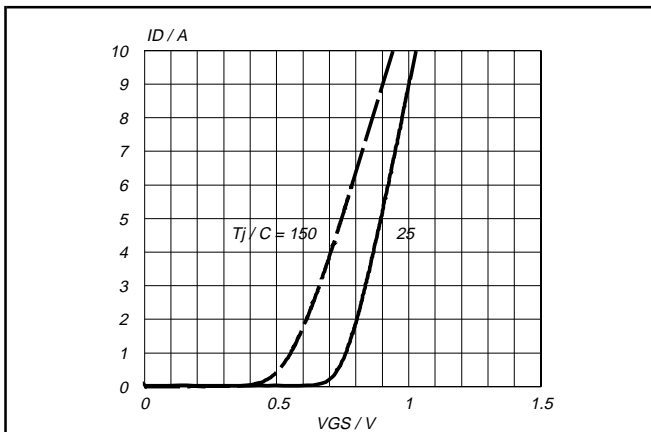


Fig. 14. Typical reverse diode current.
 $I_F = f(V_{SDS})$; conditions: $V_{GS} = 0 \text{ V}$; parameter T_j

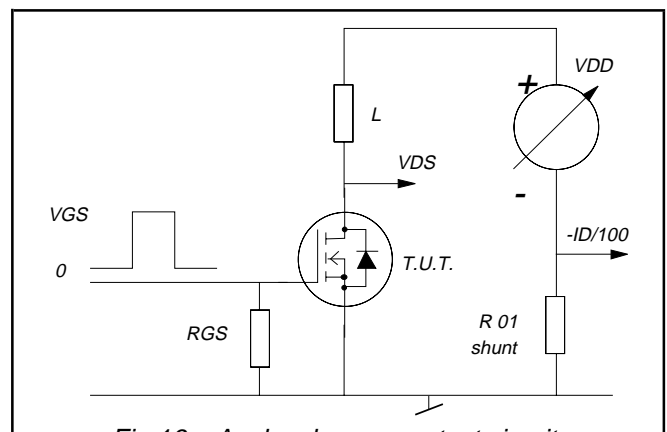
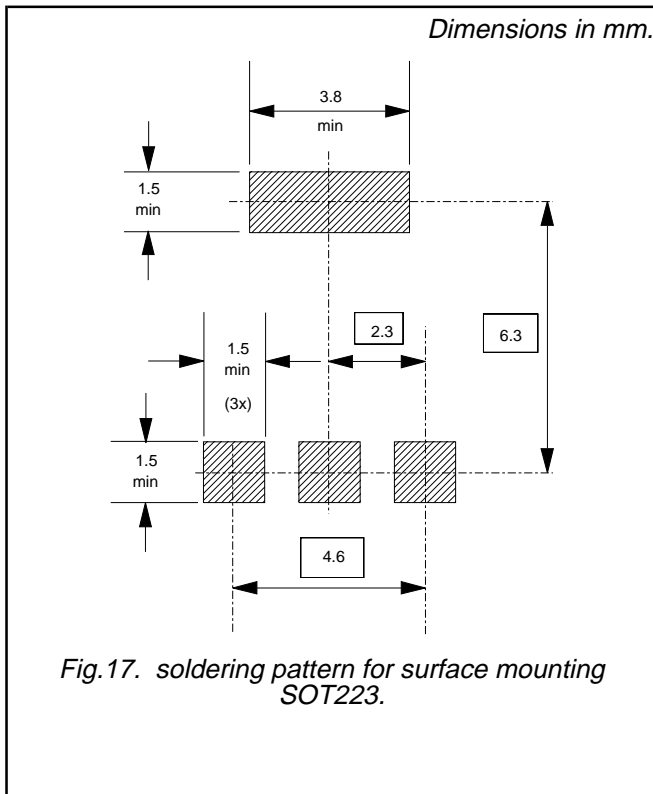


Fig. 16. Avalanche energy test circuit.
 $W_{DSS} = 0.5 \cdot L I_D^2 \cdot BV_{DSS} / (BV_{DSS} - V_{DD})$

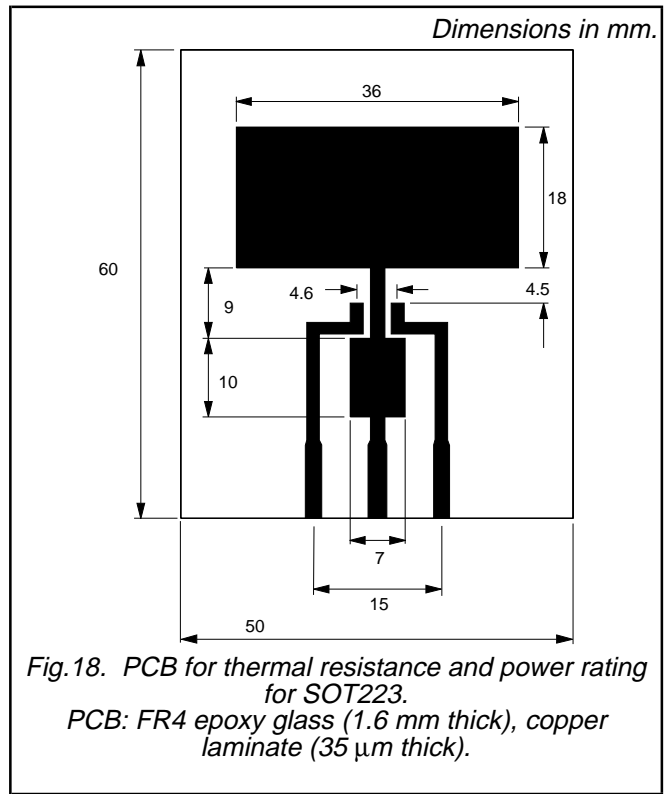
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MOUNTING INSTRUCTIONS



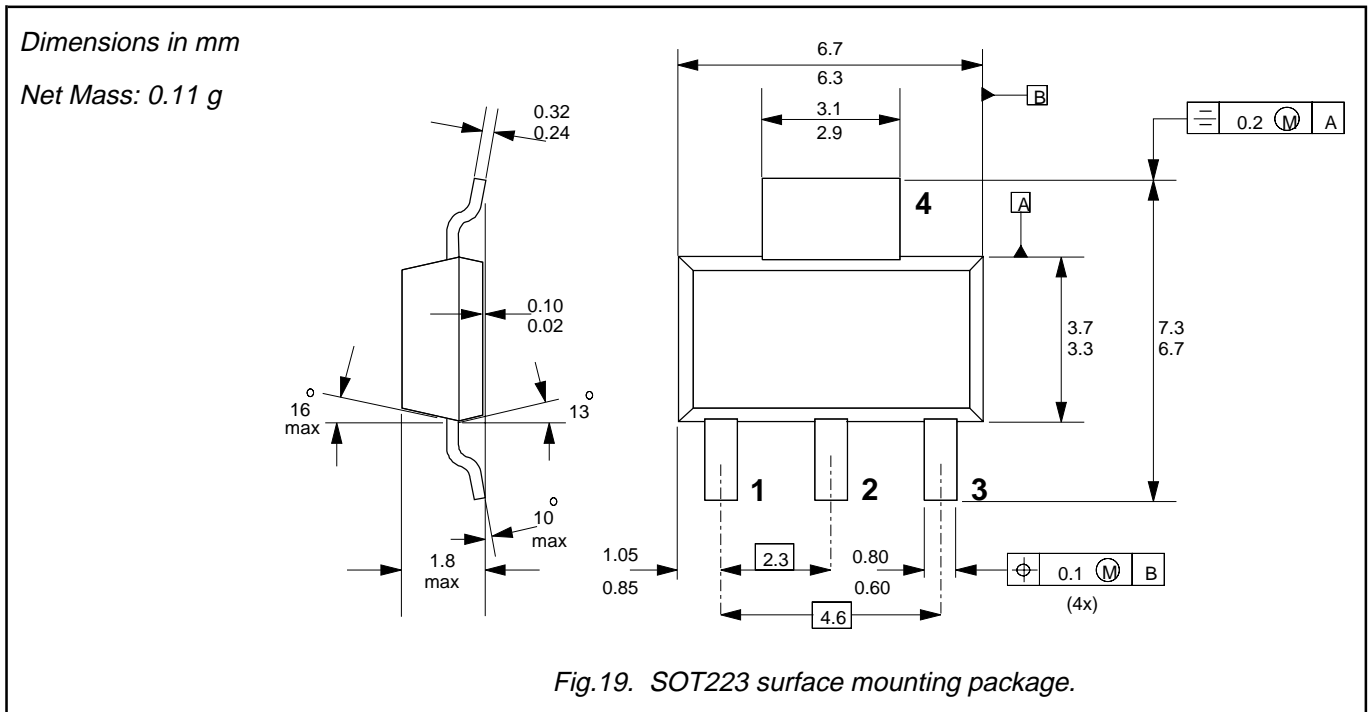
PRINTED CIRCUIT BOARD



PowerMOS transistor
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MECHANICAL DATA



Notes

1. Observe the general handling precautions for electrostatic-discharge sensitive devices (ESDs) to prevent damage to MOS gate oxide.
2. Refer to surface mounting instructions for SOT223 envelope.
3. Epoxy meets UL94 V0 at 1/8".

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BUK583-60A**DEFINITIONS**

| | |
|--|---|
| Data sheet status | |
| Objective specification | This data sheet contains target or goal specifications for product development. |
| Preliminary specification | This data sheet contains preliminary data; supplementary data may be published later. |
| Product specification | This data sheet contains final product specifications. |
| Limiting values | |
| Limiting values are given in accordance with the Absolute Maximum Rating System (IEC 134). Stress above one or more of the limiting values may cause permanent damage to the device. These are stress ratings only and operation of the device at these or at any other conditions above those given in the Characteristics sections of this specification is not implied. Exposure to limiting values for extended periods may affect device reliability. | |
| Application information | |
| Where application information is given, it is advisory and does not form part of the specification. | |
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